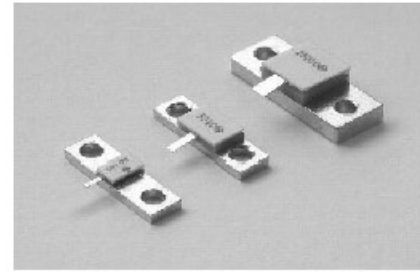


Power Flange Terminations

Features and Applications

These are high power, flanged terminations for all DC circuits up to 5GHz. The small size and wide frequency range are attained with a large heat conducting ALN substrate. Sufficient mechanical strength is attained from spattered thin metallization.

These are standard with a 50ohm resistance, a tolerance of 1% and 10W, 50W, 100W and 250W. Ni-Cr thin film technology ensures long life. Applications include: Terminations for isolator/circulators, fixed station of mobile communication electronics, and high power microwave amplifiers.



GENERAL SPECIFICATIONS

Model	Power Rating[W]	1) Maximum Power[W]	Resistance[Ω]	Tolerance(%)
TFT010	10	20	50	1.0
TFT050	30	50		
TFT100	100	200		
TFT250	250	500		

1) Test conditions: Pulse < 1second

CHARACTERISTICS

Model	TFT010	TFT050	TFT100	TFT250
Max Operating Temperature				-55℃ to +155℃
Temp. Coefficient				±50ppm/℃
Heat Resistance	6.5℃/W	2.5℃/W	1.3℃/W	0.5℃/W
VSWR at 1GHz	1.15	1.15	1.20	1.20
Storage Temperature				-55℃ to +155℃

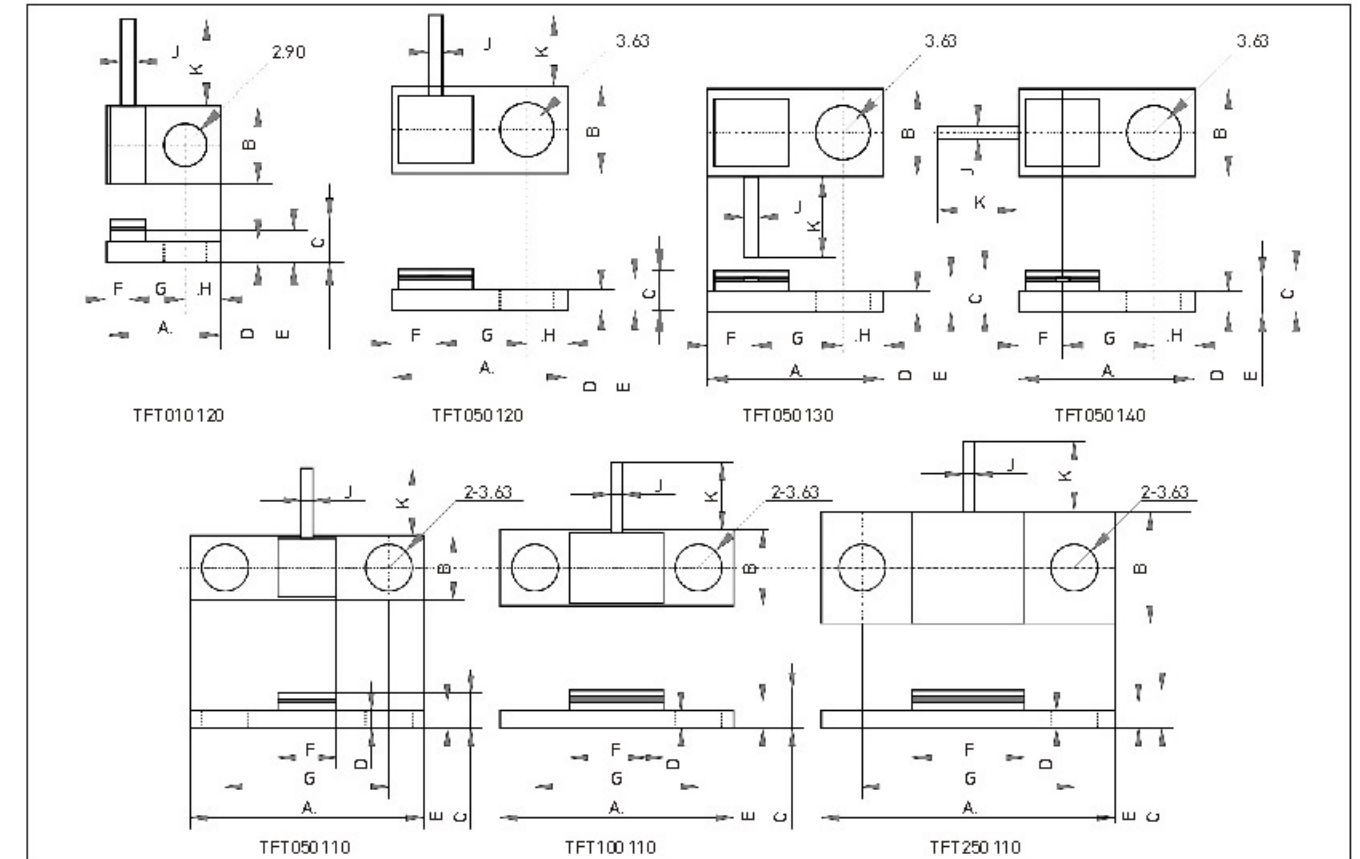
MATERIALS

Part	Material
(1) Cold end Terminal	Tin plated Ni-Cu
(2) Element	Ni-Cr
(3) Cover	ALD
(4) Substrate	ALN
(5) Flange	Ni plated Cu
(6) Beam Lead	Au plated Cu

ORDERING PROCEDURE EXAMPLE

Ordering Example	Model	Out look	TCR	Resistance	Tolerance	Bulk/Tape	Remarks
TFT010120C50ohmFZ00	TFT010	120	C	50Ω	F	200	Tray
TFT050110C50ohmFZ00	TFT050	110	C	50Ω	F	200	Tray
TFT050120C50ohmFZ00	TFT050	120	C	50Ω	F	200	Tray
TFT050130C50ohmFZ00	TFT050	130	C	50Ω	F	200	Tray
TFT050140C50ohmFZ00	TFT050	140	C	50Ω	F	200	Tray
TFT100110C50ohmFZ00	TFT100	110	C	50Ω	F	200	Tray
TFT250110C50ohmFZ00	TFT250	110	C	50Ω	F	200	Tray

DIMENSIONS (mm)



	A±0.1	B±0.1	C±0.1	D±0.1	E±0.1	F±0.1	G±0.1	H±0.1	J±0.1	K±0.1
TFT010	7.10	5.10	3.10	1.50	2.20	1.50	3.50	2.10	0.80	5.08
TFT050	13.08	6.35	3.10	1.50	2.20	(2.54)	7.49	3.05	0.80	5.08
TFT100	20.30	5.70	3.10	1.50	2.60	5.08	14.20	-	1.50	5.08
TFT250	25.00	9.53	4.50	3.00	4.10	9.52	18.42	-	3.00	5.08